

Short circuit rugged 1200 V TRENCHSTOP™ IGBT 7 technology copacked with soft and fast recovery Emitter Controlled 7 diode

Features

- $V_{CE}=1200\text{ V}$
- $I_C=8\text{ A}$
- IGBT co-packed with full current, soft and low Q_{rr} diode
- Low saturation voltage $V_{CE(sat)} = 2.0\text{ V}$ at $T_{vj}=175\text{ °C}$
- Optimized for hard switching topologies (2-L inverter, 3-L NPC T-type, ...)
- Short circuit ruggedness $8\text{ }\mu\text{sec}$
- Wide range of dv/dt controllability
- Complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>

Potential applications

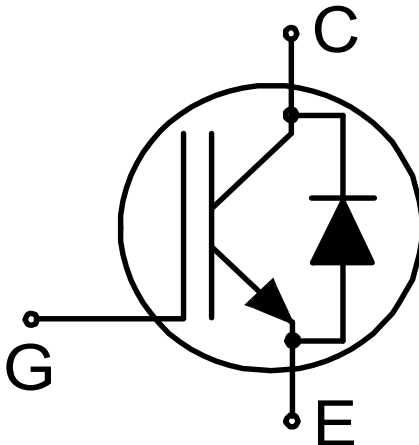
- Industrial Drives
- Industrial Power Supplies
- Solar Inverters

Product validation

- Product Validation: Qualified for industrial applications according to the relevant tests of JEDEC47/20/22



Description



Type	Package	Marking
IKW08N120CS7	PG-TO247-3	K08MCS7



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1 Package

1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5mm. (0.197in) from case	L_E			13.0		nH
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature		wave soldering 1.6mm (0.063in.) from case for 10s			260	°C
Mounting torque , M3 screw Maximum of mounting process: 3	M				0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W

2 IGBT

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CE}	$T_{vj} \geq 25\text{ °C}$		1200	V
DC collector current, limited by T_{vjmax}	I_C		$T_C = 25\text{ °C}$	21	A
			$T_C = 100\text{ °C}$	14	
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}			24	A
Turn-off safe operating area		$V_{CE} \leq 1200\text{ V}, T_{vj} \leq 175\text{ °C}$		24	A
Gate-emitter voltage	V_{GE}			± 20	V
Transient gate-emitter voltage	V_{GE}	$t_p \leq 0.5\text{ }\mu\text{s}, D < 0.001$		± 25	V
Short circuit withstand time	t_{SC}	$V_{CC} \leq 600\text{ V}, V_{GE} = 15\text{ V}$, Allowed number of short circuits < 1000, Time between short circuits $\geq 1.0\text{ s}$, $T_{vj} = 150\text{ °C}$		8	μs
Power dissipation	P_{tot}		$T_C = 25\text{ °C}$	106	W
			$T_C = 100\text{ °C}$	53	

Table 3 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\text{ sat}}$	$I_C = 8.0\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$		1.65	2.00	V
			$T_{vj} = 175\text{ °C}$		2.00		

Table 3 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Gate-emitter threshold voltage	V_{GEth}	$I_C = 0.16 \text{ mA}$, $V_{CE} = V_{GE}$, $T_{vj} = 25 \text{ °C}$	5.15	5.70	6.45	V
Zero gate voltage collector current	I_{CES}	$V_{CE} = 1200 \text{ V}$, $V_{GE} = 0 \text{ V}$, $T_{vj} = 25 \text{ °C}$			40	μA
		$T_{vj} = 175 \text{ °C}$		750		
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = 20 \text{ V}$			100	nA
Transconductance	g_{fs}	$I_C = 8.0 \text{ A}$, $V_{CE} = 20 \text{ V}$, $T_{vj} = 175 \text{ °C}$		3.5		S
Short circuit collector current	I_{SC}	$V_{CC} \leq 600 \text{ V}$, $V_{GE} = 15 \text{ V}$, $t_{SC} \leq 8 \text{ }\mu\text{s}$, Allowed number of short circuits < 1000, Time between short circuits $\geq 1.0 \text{ s}$, $T_{vj} = 25 \text{ °C}$		50		A
Input capacitance	C_{ies}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 100 \text{ kHz}$		1.2		nF
Output capacitance	C_{oes}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 100 \text{ kHz}$		33		pF
Reverse transfer capacitance	C_{res}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 100 \text{ kHz}$		5.5		pF
Gate charge	Q_G	$I_C = 8.0 \text{ A}$, $V_{GE} = 15 \text{ V}$, $V_{CE} = 960 \text{ V}$		52		nC
Turn-on delay time	t_{don}	$V_{CE} = 600 \text{ V}$, $V_{GE} = 15 \text{ V}$, $R_{Gon} = 20.0 \text{ }\Omega$, $R_{Goff} = 20.0 \text{ }\Omega$, $T_{vj} = 25 \text{ °C}$, $I_C = 8.0 \text{ A}$		17		ns
		$T_{vj} = 175 \text{ °C}$, $I_C = 8.0 \text{ A}$		16		
Rise time (inductive load)	t_r	$V_{CE} = 600 \text{ V}$, $V_{GE} = 15 \text{ V}$, $R_{Gon} = 20.0 \text{ }\Omega$, $R_{Goff} = 20.0 \text{ }\Omega$, $T_{vj} = 25 \text{ °C}$, $I_C = 8.0 \text{ A}$		12		ns
		$T_{vj} = 175 \text{ °C}$, $I_C = 8.0 \text{ A}$		15		
Turn-off delay time	t_{doff}	$V_{CE} = 600 \text{ V}$, $V_{GE} = 15 \text{ V}$, $R_{Gon} = 20.0 \text{ }\Omega$, $R_{Goff} = 20.0 \text{ }\Omega$, $T_{vj} = 25 \text{ °C}$, $I_C = 8.0 \text{ A}$		160		ns
		$T_{vj} = 175 \text{ °C}$, $I_C = 8.0 \text{ A}$		245		
Fall time (inductive load)	t_f	$V_{CE} = 600 \text{ V}$, $V_{GE} = 15 \text{ V}$, $R_{Gon} = 20.0 \text{ }\Omega$, $R_{Goff} = 20.0 \text{ }\Omega$, $T_{vj} = 25 \text{ °C}$, $I_C = 8.0 \text{ A}$		95		ns
		$T_{vj} = 175 \text{ °C}$, $I_C = 8.0 \text{ A}$		255		
Turn-on energy	E_{on}	$V_{CE} = 600 \text{ V}$, $V_{GE} = 15 \text{ V}$, $R_{Gon} = 20.0 \text{ }\Omega$, $R_{Goff} = 20.0 \text{ }\Omega$, $T_{vj} = 25 \text{ °C}$, $I_C = 8.0 \text{ A}$		0.37		mJ
		$T_{vj} = 175 \text{ °C}$, $I_C = 8.0 \text{ A}$		0.59		
Turn-off energy	E_{off}	$V_{CE} = 600 \text{ V}$, $V_{GE} = 15 \text{ V}$, $R_{Gon} = 20.0 \text{ }\Omega$, $R_{Goff} = 20.0 \text{ }\Omega$, $T_{vj} = 25 \text{ °C}$, $I_C = 8.0 \text{ A}$		0.40		mJ
		$T_{vj} = 175 \text{ °C}$, $I_C = 8.0 \text{ A}$		0.86		

Table 3 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Total switching energy	E_{ts}	$V_{CE} = 600 \text{ V}$, $V_{GE} = 15 \text{ V}$, $R_{Gon} = 20.0 \Omega$, $R_{Goff} = 20.0 \Omega$		0.77		mJ
				1.45		
IGBT thermal resistance, junction-case	R_{thjc}			1.05	1.42	K/W
Operating junction temperature	T_{vj}		-40		175	°C

3 Diode

Table 4 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} \geq 25 \text{ °C}$	1200	V
Diode forward current, limited by T_{vjmax}	I_F	$T_C = 25 \text{ °C}$	18	A
		$T_C = 100 \text{ °C}$	12	
Diode pulsed current, limited by T_{vjmax}	I_{Fpuls}		24	A
Power dissipation	P_{tot}	$T_C = 25 \text{ °C}$	62	W
		$T_C = 100 \text{ °C}$	31	

Table 5 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Diode forward voltage	V_F	$I_F = 8.0 \text{ A}$		1.65	2.15	V
				1.60		
Reverse leakage current	I_R	$V_R = 1200 \text{ V}$			40	μA
				750		
Diode reverse recovery time	t_{rr}	$V_R = 600 \text{ V}$, $R_{Gon} = 20.0 \Omega$		130		ns
				210		
Diode reverse recovery charge	Q_{rr}	$V_R = 600 \text{ V}$, $R_{Gon} = 20.0 \Omega$		0.45		μC
				1.10		

Table 5 **Characteristic values (continued)**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Diode peak reverse recovery current	I_{rrm}	$V_R = 600 \text{ V}, R_{Gon} = 20.0 \text{ } \Omega$		$T_{vj} = 25 \text{ } ^\circ\text{C}, I_F = 8.0 \text{ A}$	9.0	A
				$T_{vj} = 175 \text{ } ^\circ\text{C}, I_F = 8.0 \text{ A}$	13.0	
Diode peak rate off fall of reverse recovery current	di_{rr}/dt	$V_R = 600 \text{ V}, R_{Gon} = 20.0 \text{ } \Omega$		$T_{vj} = 25 \text{ } ^\circ\text{C}, I_F = 8.0 \text{ A}$	-110	A/ μs
				$T_{vj} = 175 \text{ } ^\circ\text{C}, I_F = 8.0 \text{ A}$	-95	
Reverse recovery energy	E_{rec}	$V_R = 600 \text{ V}, R_{Gon} = 20.0 \text{ } \Omega$		$T_{vj} = 25 \text{ } ^\circ\text{C}, I_F = 8.0 \text{ A}$	0.13	mJ
				$T_{vj} = 175 \text{ } ^\circ\text{C}, I_F = 8.0 \text{ A}$	0.37	
Diode thermal resistance, junction-case	R_{thjc}			1.80	2.40	K/W
Operating junction temperature	T_{vj}		-40		175	$^\circ\text{C}$

Note: *For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.*

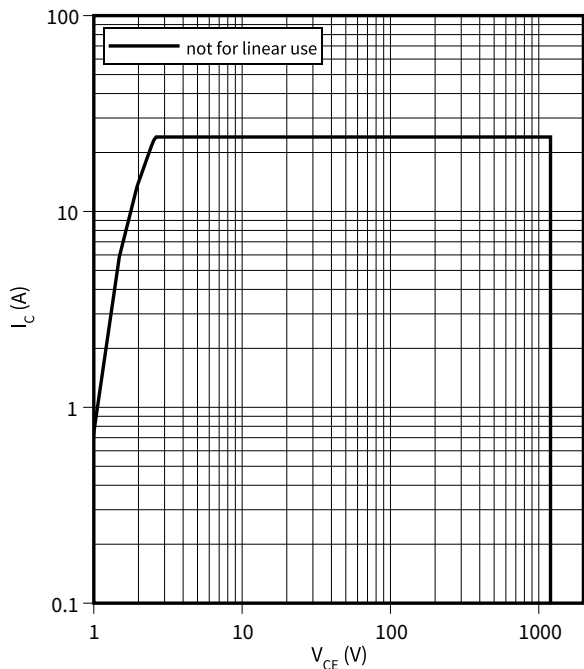
Dynamic test circuit, parasitic inductance $L_\sigma = 30 \text{ nH}$, $C_\sigma = 4 \text{ pF}$

4 Characteristics diagrams

4 Characteristics diagrams

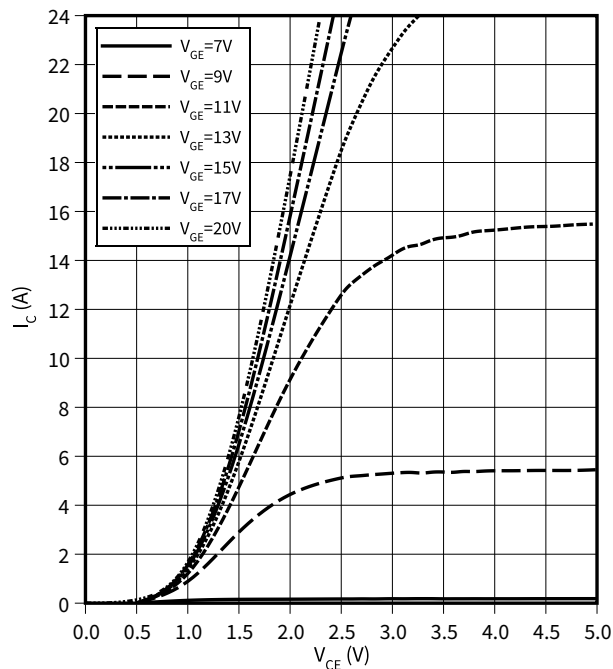
Reverse bias safe operating area, IGBT

$I_C = f(V_{CE})$
 $T_{vj} \leq 175\text{ °C}$, $V_{GE} = 15\text{ V}$



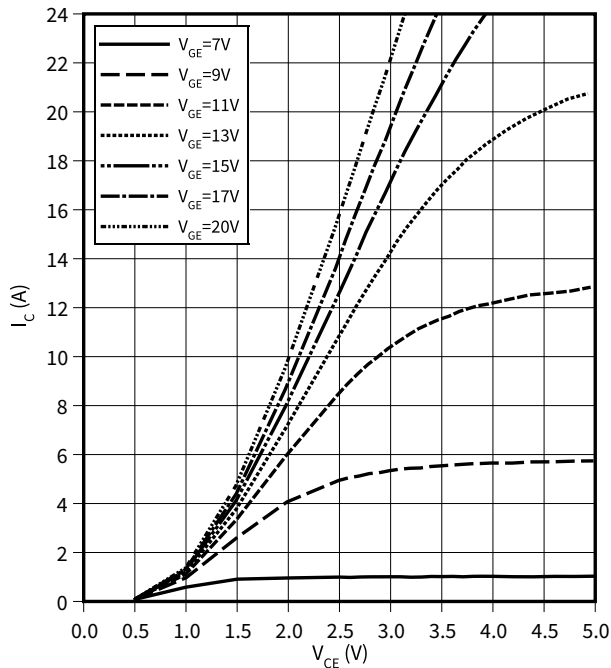
Typical output characteristic, IGBT

$I_C = f(V_{CE})$
 $T_{vj} = 25\text{ °C}$



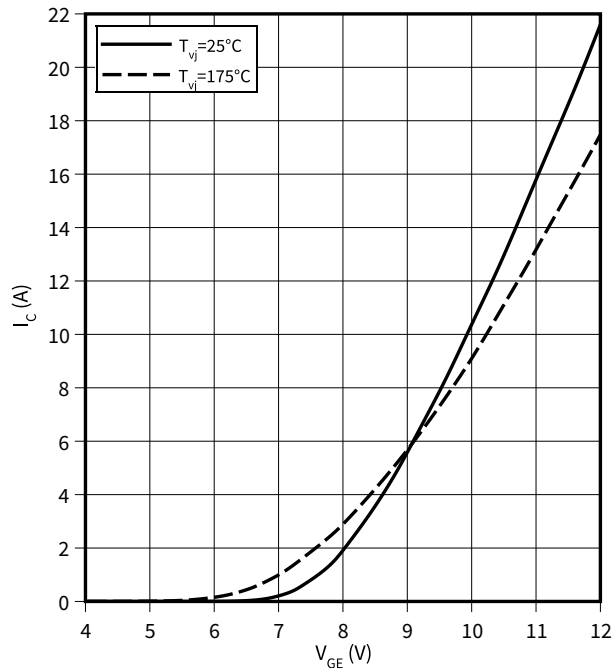
Typical output characteristic, IGBT

$I_C = f(V_{CE})$
 $T_{vj} = 175\text{ °C}$



Typical transfer characteristic, IGBT

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$

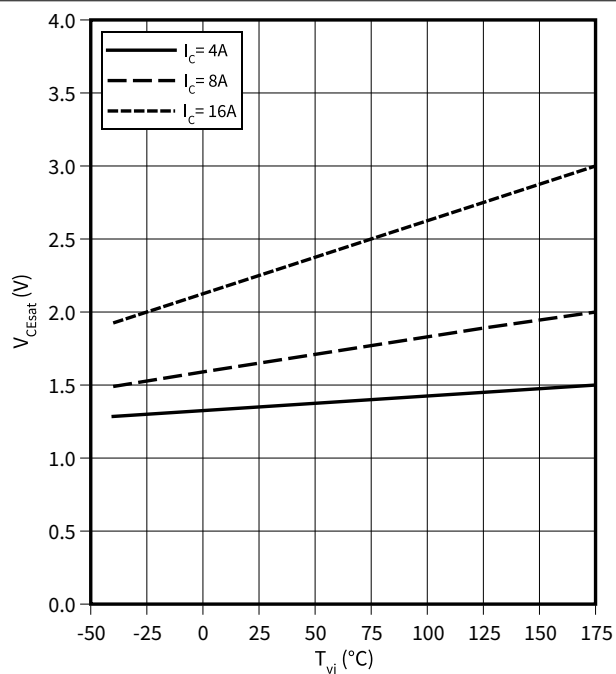


4 Characteristics diagrams

Typical collector-emitter saturation voltage as a function of junction temperature, IGBT

$$V_{CEsat} = f(T_{vj})$$

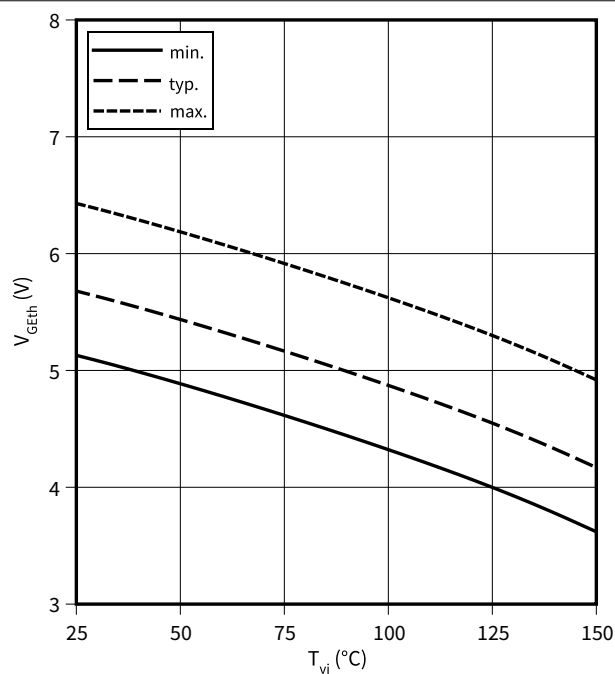
$$V_{GE} = 15 \text{ V}$$



Gate-emitter threshold voltage as a function of junction temperature, IGBT

$$V_{GEth} = f(T_{vj})$$

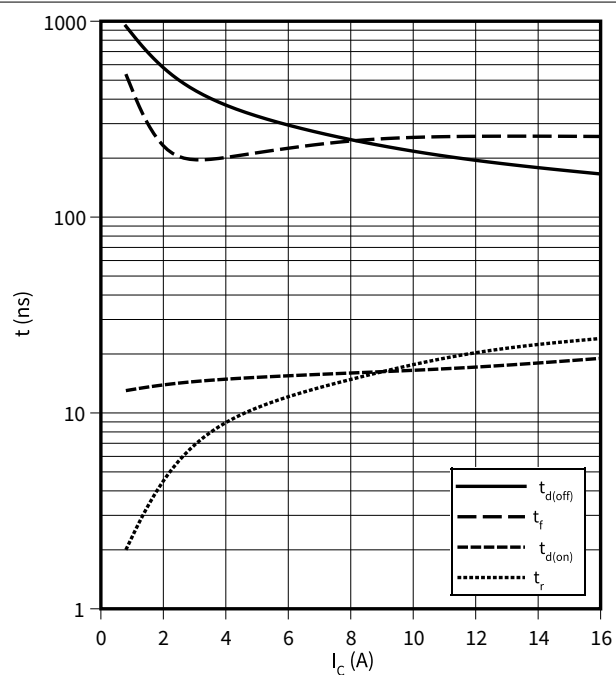
$$I_C = 0.16 \text{ mA}$$



Typical switching times as a function of collector current, IGBT

$$t = f(I_C)$$

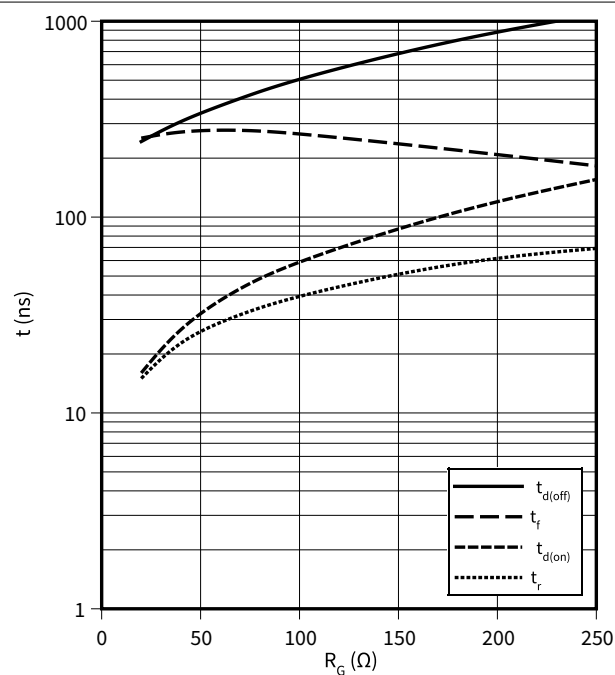
$$V_{CE} = 600 \text{ V}, T_{vj} = 175 \text{ °C}, V_{GE} = 0/15 \text{ V}, R_G = 20.0 \text{ } \Omega$$



Typical switching times as a function of gate resistor, IGBT

$$t = f(R_G)$$

$$I_C = 8.0 \text{ A}, V_{CE} = 600 \text{ V}, T_{vj} = 175 \text{ °C}, V_{GE} = 0/15 \text{ V}$$

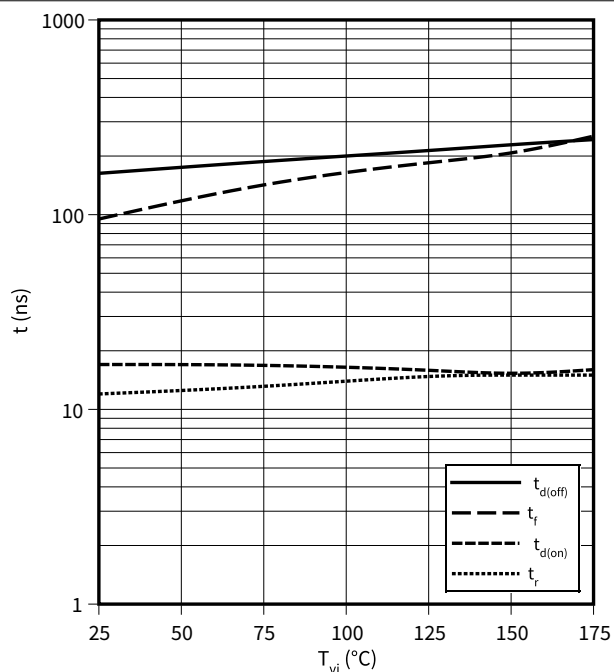


4 Characteristics diagrams

Typical switching times as a function of junction temperature, IGBT

$$t = f(T_{vj})$$

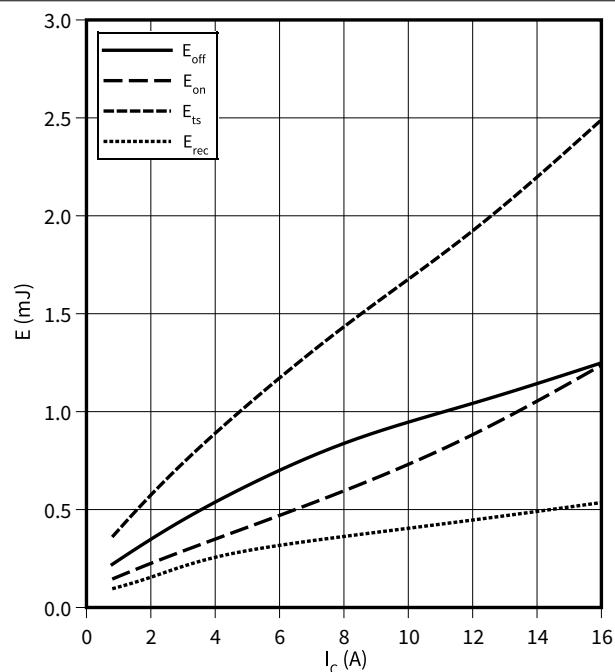
$I_C = 8.0 \text{ A}$, $V_{CE} = 600 \text{ V}$, $V_{GE} = 0/15 \text{ V}$, $R_G = 20.0 \Omega$



Typical switching energy losses as a function of collector current, IGBT

$$E = f(I_C)$$

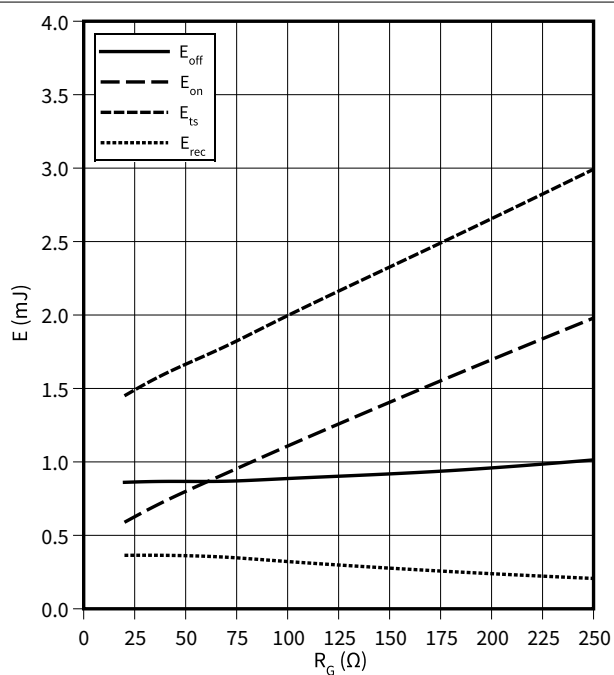
$V_{CE} = 600 \text{ V}$, $T_{vj} = 175 \text{ °C}$, $V_{GE} = 0/15 \text{ V}$, $R_G = 20.0 \Omega$



Typical switching energy losses as a function of gate resistor, IGBT

$$E = f(R_G)$$

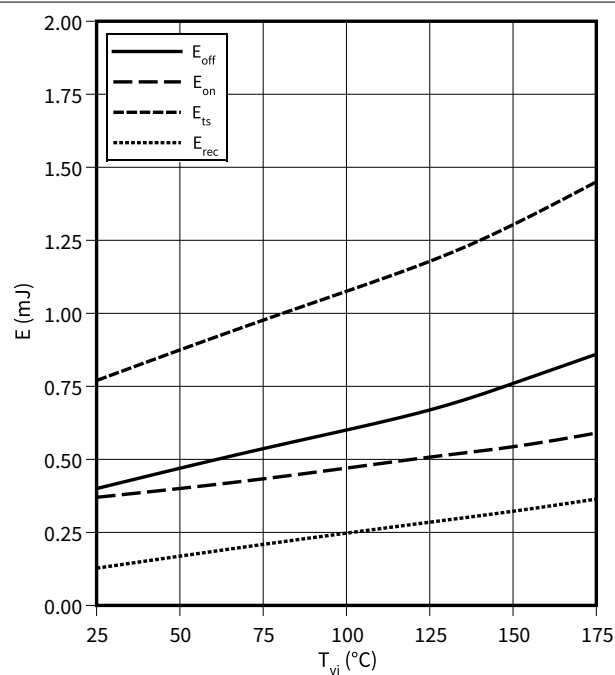
$I_C = 8.0 \text{ A}$, $V_{CE} = 600 \text{ V}$, $T_{vj} = 175 \text{ °C}$, $V_{GE} = 0/15 \text{ V}$



Typical switching energy losses as a function of junction temperature, IGBT

$$E = f(T_{vj})$$

$I_C = 8.0 \text{ A}$, $V_{CE} = 600 \text{ V}$, $V_{GE} = 0/15 \text{ V}$, $R_G = 20.0 \Omega$

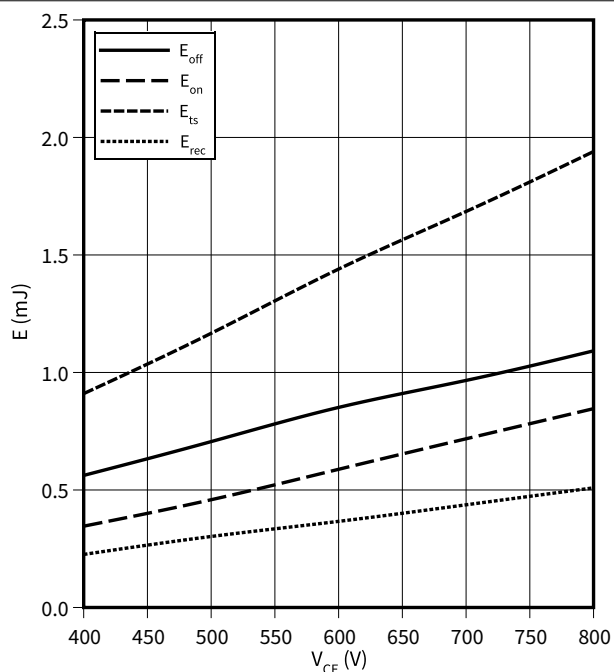


4 Characteristics diagrams

Typical switching energy losses as a function of collector emitter voltage, IGBT

$$E = f(V_{CE})$$

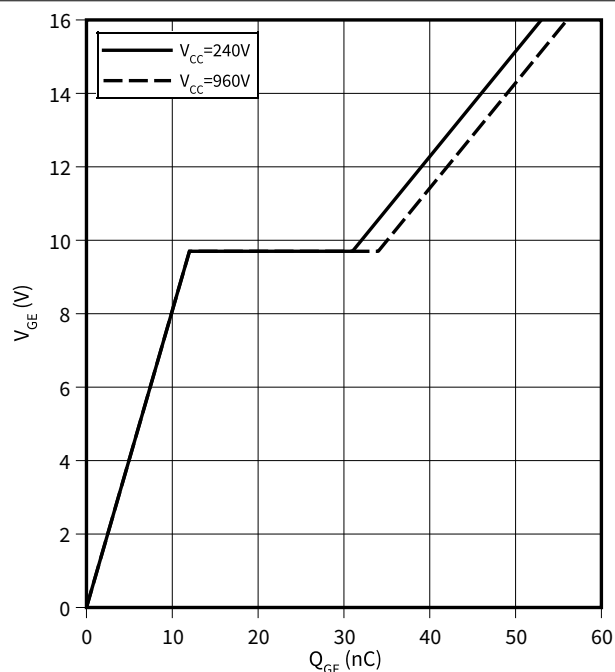
$I_C = 8.0 \text{ A}$, $T_{vj} = 175 \text{ }^\circ\text{C}$, $V_{GE} = 0/15 \text{ V}$, $R_G = 20.0 \text{ } \Omega$



Typical gate charge, IGBT

$$V_{GE} = f(Q_{GE})$$

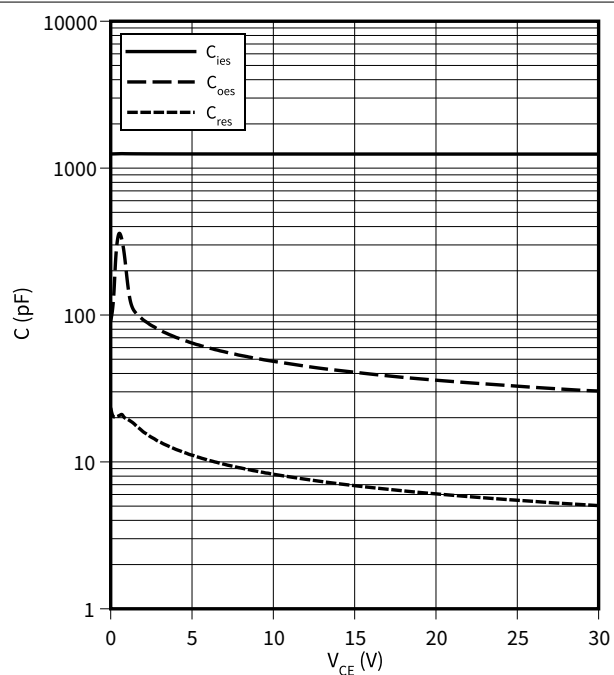
$I_C = 8.0 \text{ A}$



Typical capacitance as a function of collector-emitter voltage, IGBT

$$C = f(V_{CE})$$

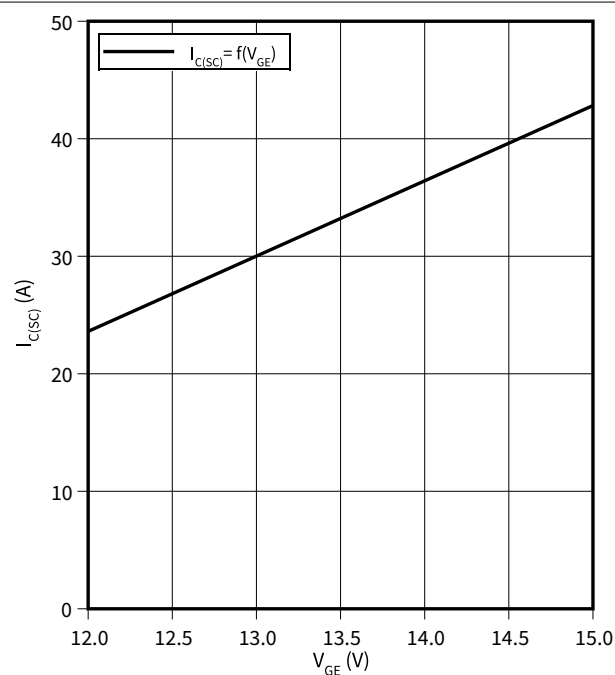
$f = 100 \text{ kHz}$, $V_{GE} = 0 \text{ V}$



Typical short circuit collector current as a function of gate-emitter voltage, IGBT

$$I_{C(SC)} = f(V_{GE})$$

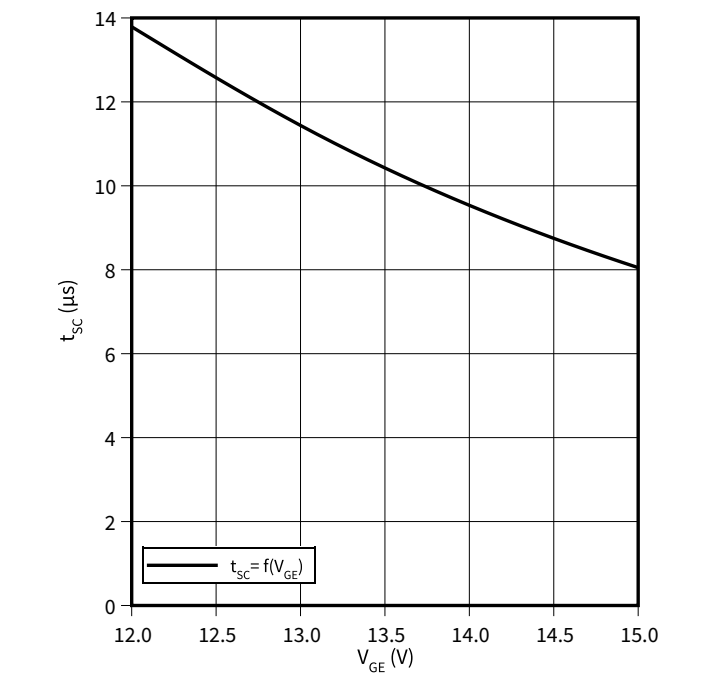
$T_{vj} = 150 \text{ }^\circ\text{C}$, $V_{CC} = 600 \text{ V}$



4 Characteristics diagrams

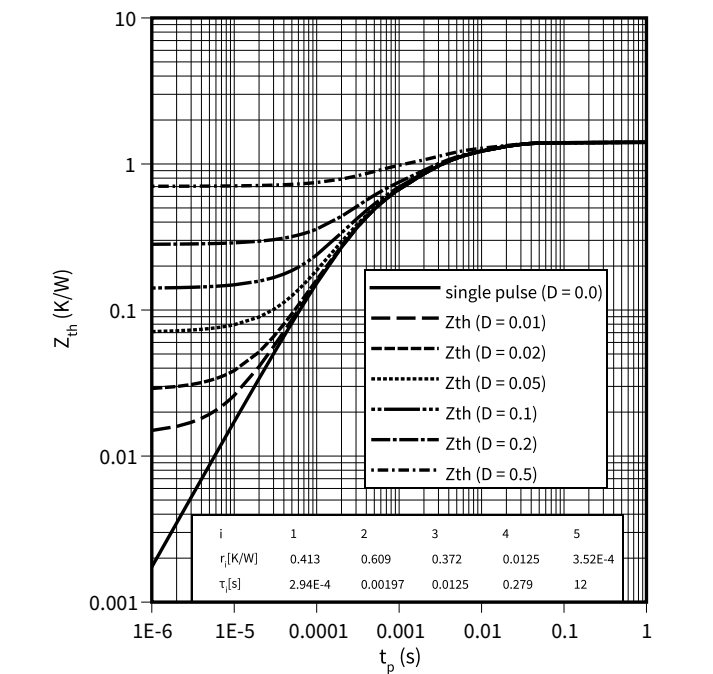
Short circuit withstand time as a function of gate-emitter voltage, IGBT

$t_{SC} = f(V_{GE})$
 $T_{vj} \leq 150\text{ }^{\circ}\text{C}, V_{CC} = 600\text{ V}$



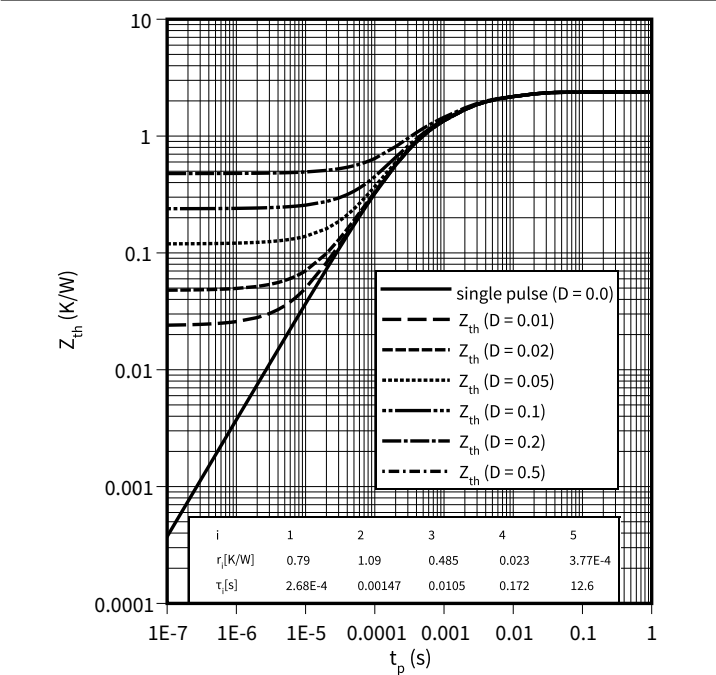
IGBT transient thermal impedance, IGBT

$Z_{th} = f(t_p)$
 $D = t_p/T$



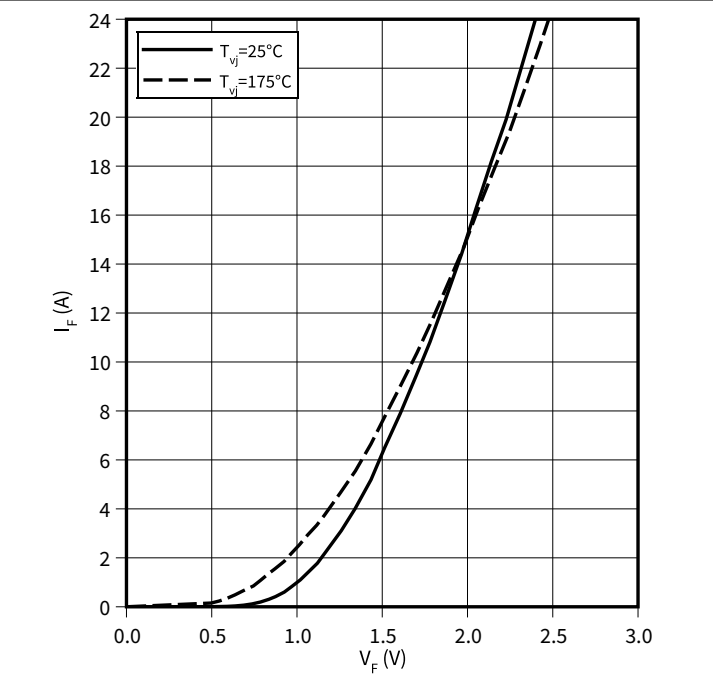
Diode transient thermal impedance as a function of pulse width, Diode

$Z_{th} = f(t_p)$
 $D = t_p/T$



Typical diode forward current as a function of forward voltage, Diode

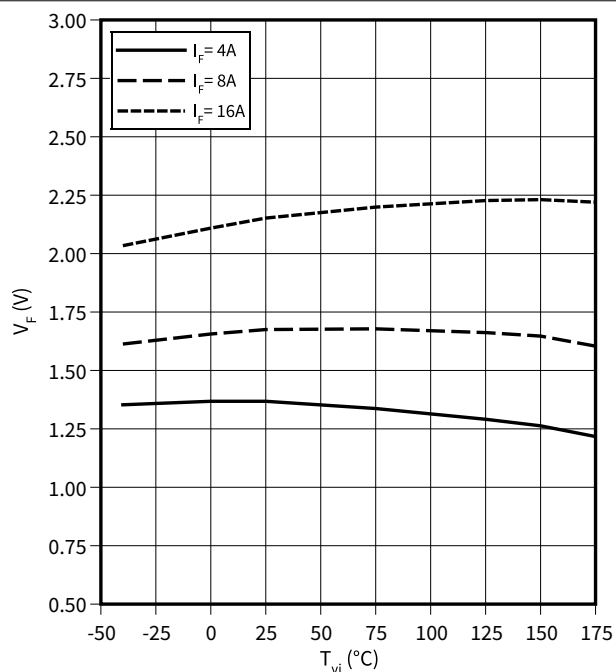
$I_F = f(V_F)$



4 Characteristics diagrams

Typical diode forward voltage as a function of junction temperature, Diode

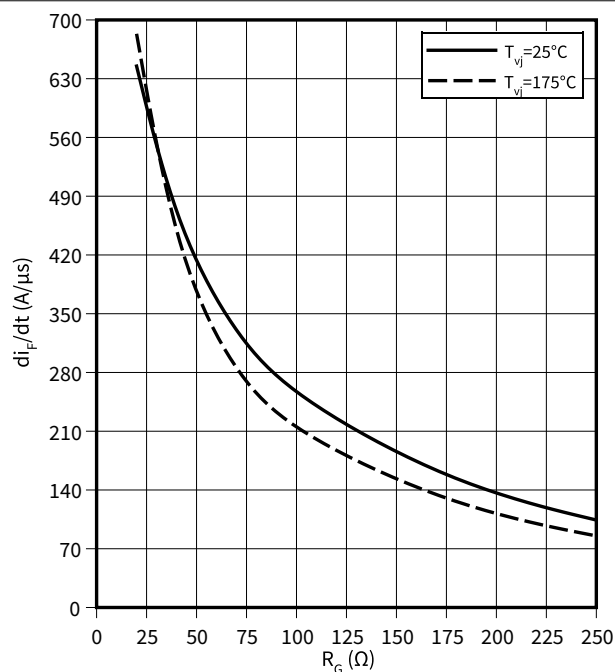
$$V_F = f(T_{vj})$$



Typical diode current slope as a function of gate resistor, Diode

$$di_F/dt = f(R_G)$$

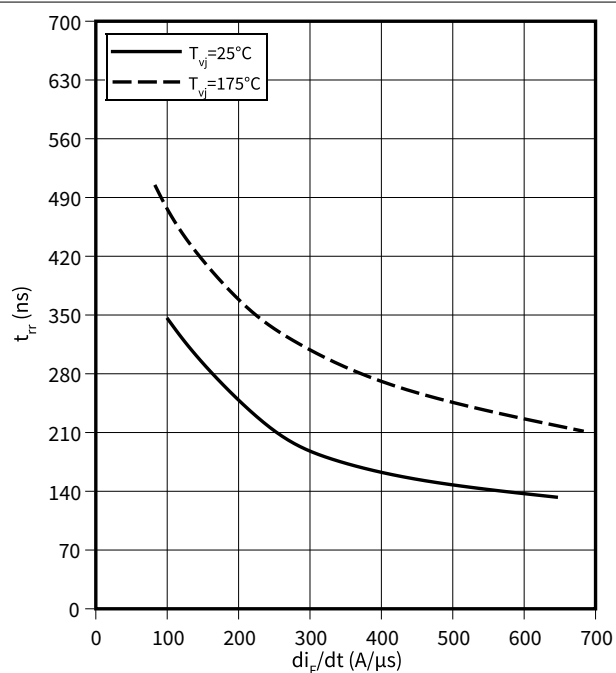
$$I_C = 8.0 A, V_{CE} = 600 V, V_{GE} = 0/15 V$$



Typical reverse recovery time as a function of diode current slope, Diode

$$t_{rr} = f(di_F/dt)$$

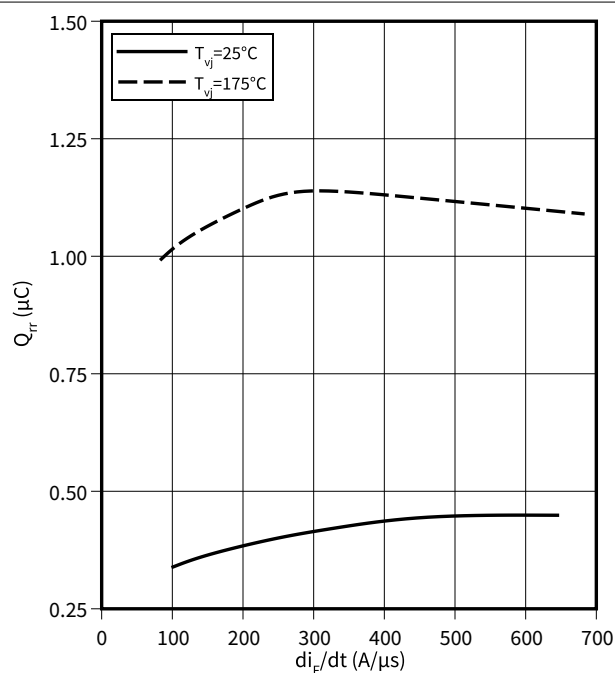
$$V_R = 600 V, I_F = 8.0 A$$



Typical reverse recovery charge as a function of diode current slope, Diode

$$Q_{rr} = f(di_F/dt)$$

$$V_R = 600 V, I_F = 8.0 A$$

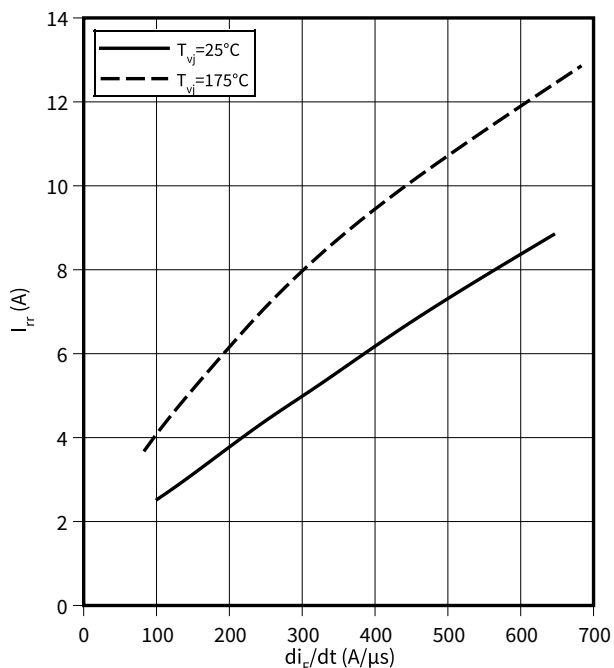


4 Characteristics diagrams

Typical reverse recovery current as a function of diode current slope, Diode

$$I_{rr} = f(di_F/dt)$$

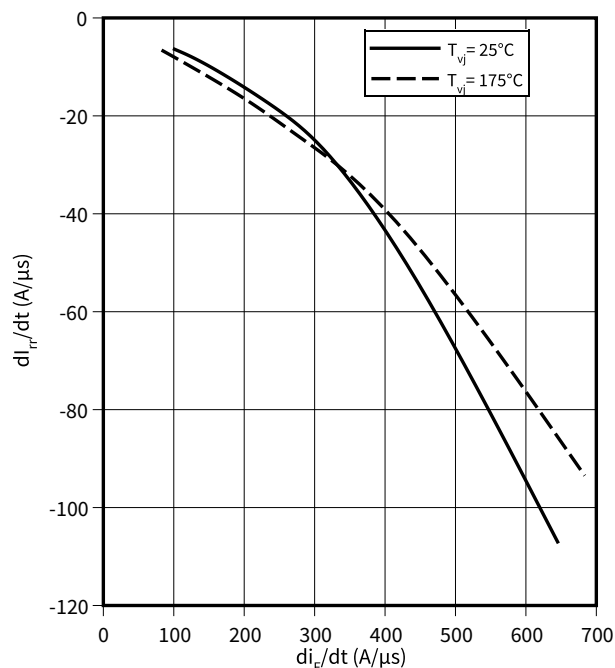
$V_R = 600 \text{ V}$, $I_F = 8.0 \text{ A}$



Typical diode peak rate of fall of reverse recovery current as a function of diode current slope, Diode

$$dI_{rr}/dt = f(di_F/dt)$$

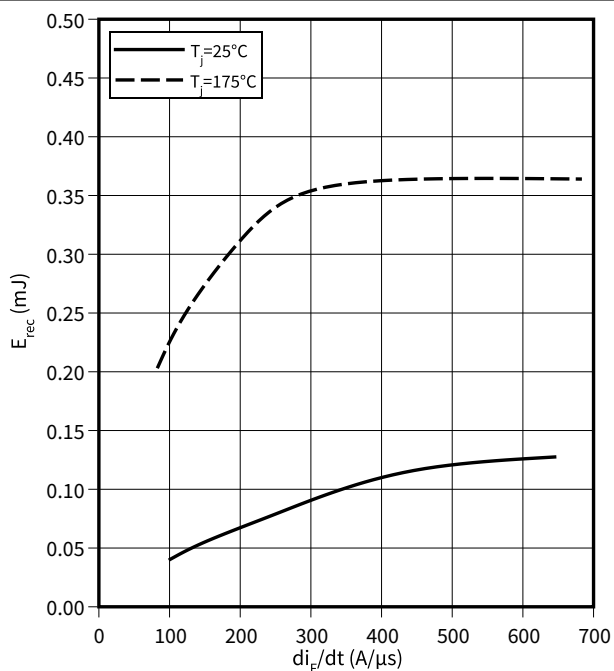
$V_R = 600 \text{ V}$, $I_F = 8.0 \text{ A}$



Typical reverse energy losses as a function of diode current slope, Diode

$$E_{rec} = f(di_F/dt)$$

$V_R = 600 \text{ V}$, $I_F = 8.0 \text{ A}$



5 Package outlines

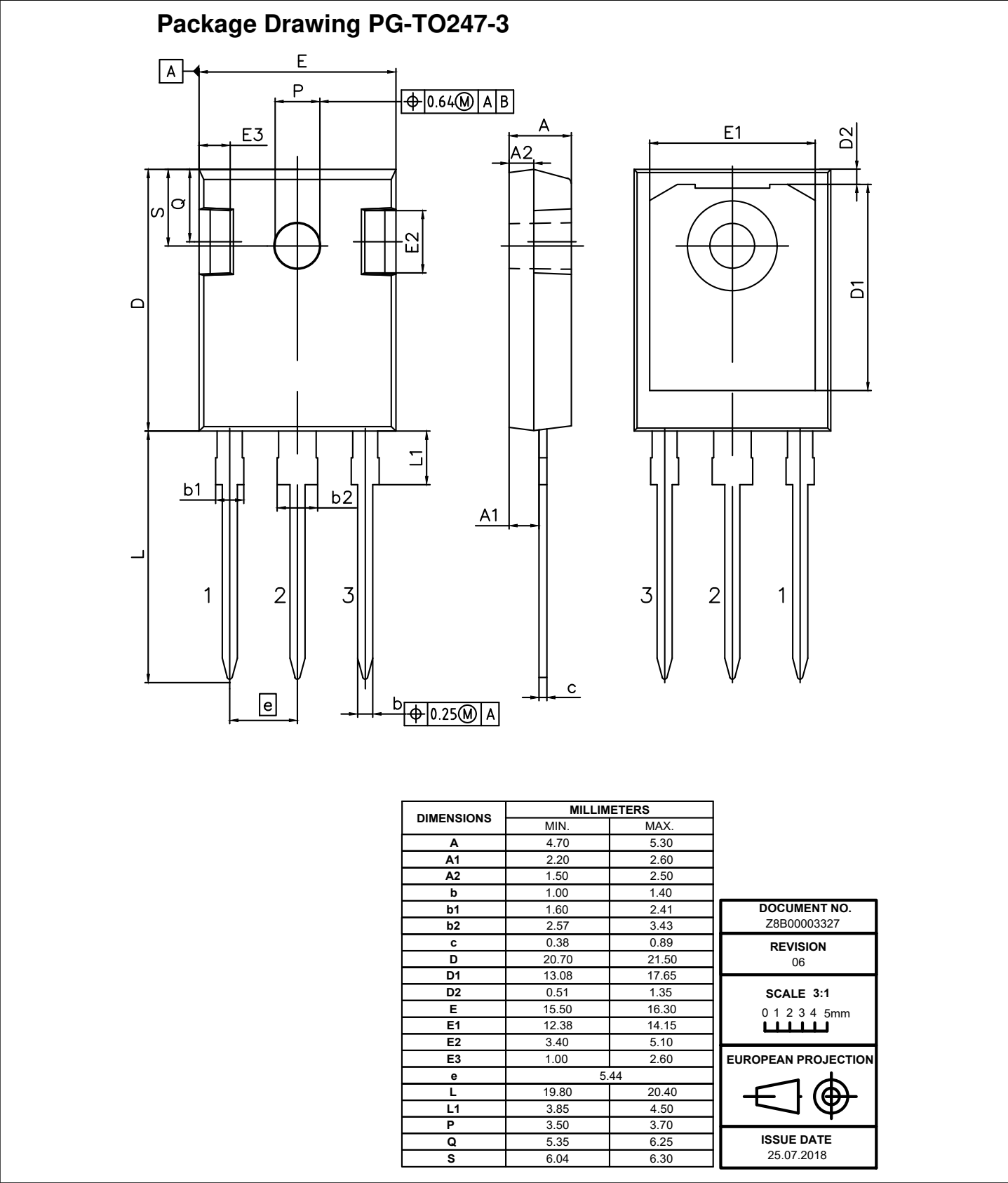


Figure 6

6 Testing conditions

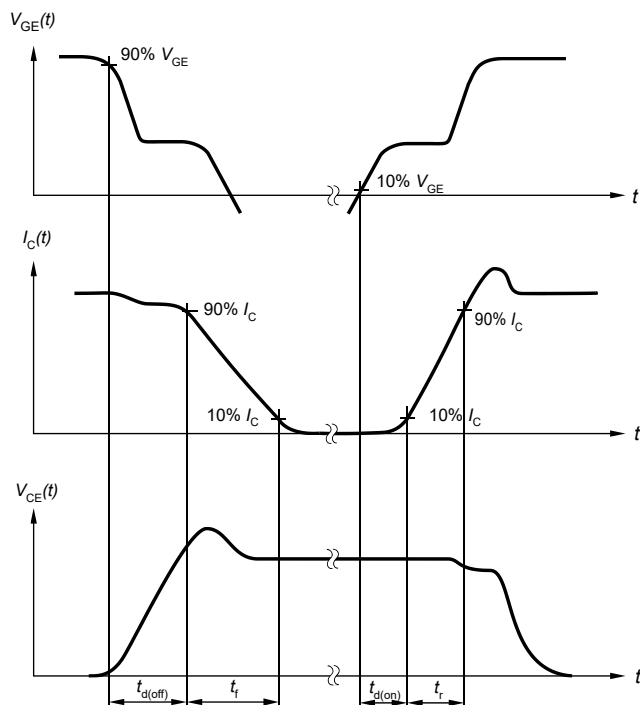


Figure A. Definition of switching times

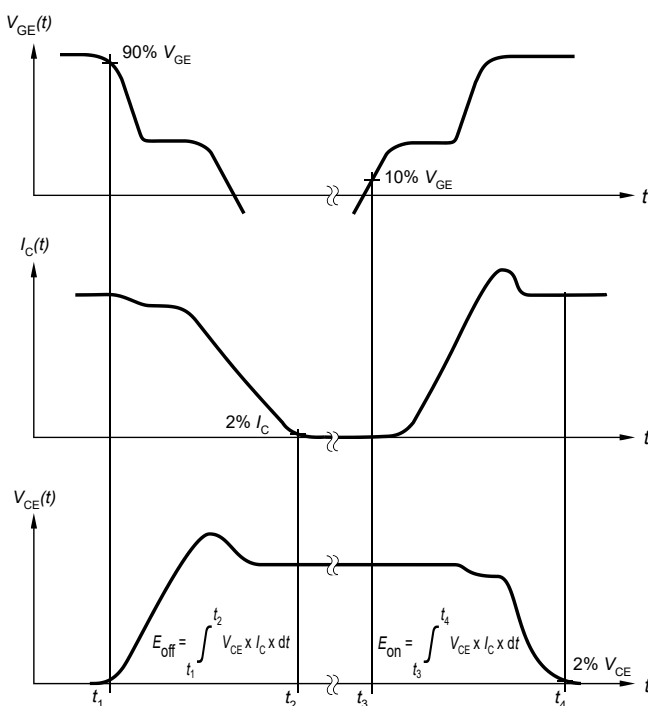


Figure B. Definition of switching losses

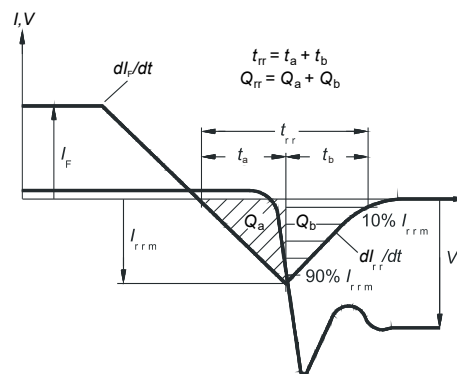


Figure C. Definition of diode switching characteristics

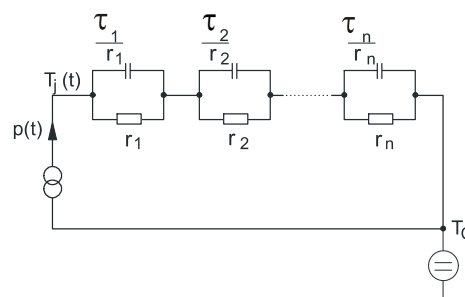


Figure D. Thermal equivalent circuit

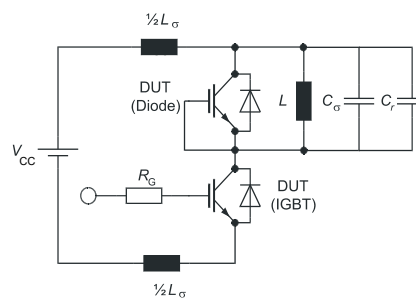


Figure E. **Dynamic test circuit**
 Parasitic inductance L_{σ} ,
 parasitic capacitor C_{σ} ,
 relief capacitor C_r ,
 (only for ZVT switching)

Figure 7

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